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# 1. Global joint venture starts operations as WeEn Semiconductors

Dear customer,

As from November 9th, 2015 NXP Semiconductors N.V. and Beijing JianGuang Asset Management Co. Ltd established Bipolar Power joint venture (JV), **WeEn Semiconductors**, which will be used in future Bipolar Power documents together with new contact details.

In this document where the previous NXP references remain, please use the new links as shown below.

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Thank you for your cooperation and understanding,

WeEn Semiconductors





**Product data sheet** 

# 1. General description

Hyperfast power diode in a SOT404 (D2PAK) surface-mountable plastic package.

# 2. Features and benefits

- Fast switching
- Surface-mountable package
- Low leakage current
- Low reverse recovery current
- Low thermal resistance
- Reduces switching losses in associated MOSFET

# 3. Applications

- Continuous Current Mode (CCM) Power Factor Correction (PFC)
- Half-bridge/full-bridge switched-mode power supplies

# 4. Quick reference data

| Table 1. Qui            | ck reference data               |   |  |     |     |     |      |
|-------------------------|---------------------------------|---|--|-----|-----|-----|------|
| Symbol                  | Parameter                       | Conditions  |  | Min | Тур | Max | Unit |
| V <sub>RRM</sub>        | repetitive peak reverse voltage |   |  | -   | -   | 600 | V    |
| I <sub>F(AV)</sub>      | average forward current         | $\delta$ = 0.5; T <sub>mb</sub> ≤ 130 °C; square-wave<br>pulse; <u>Fig. 1</u> ; <u>Fig. 2</u> ; <u>Fig. 3</u> |  | -   | -   | 8   | A    |
| Static charact          | eristics                        | ·   |  |     |     |     |      |
| V <sub>F</sub>          | forward voltage                 | I <sub>F</sub> = 8 A; T <sub>j</sub> = 125 °C; <u>Fig. 6</u>  |  | -   | 1.5 | 1.9 | V    |
| Dynamic characteristics |                                 |   |  |     |     |     |      |
| t <sub>rr</sub>         | reverse recovery time           | $I_F$ = 1 A; V <sub>R</sub> = 30 V; dI <sub>F</sub> /dt = 200 A/µs;<br>T <sub>j</sub> = 25 °C; <u>Fig. 7</u>  |  | -   | 12  | 18  | ns   |





Hyperfast power diode

# 5. Pinning information

| Table 2. | Pinning | information                         |                    |                |  |
|----------|---------|-------------------------------------|--------------------|----------------|--|
| Pin      | Symbol  | Description                         | Simplified outline | Graphic symbol |  |
| 1        | n.c.    | no connection                       | mb                 | к — К — А      |  |
| 2        | К       | cathode[1]                          |                    | 001aaa020      |  |
| 3        | А       | anode                               |                    | i              |  |
| mb       | К       | mounting base; connected to cathode | D2PAK (SOT404)     |                |  |

[1] It is not possible to connect to pin 2 of the SOT404 package.

# 6. Ordering information

| Table 3.       Ordering information |         |  |         |  |  |  |
|-------------------------------------|---------|--|---------|--|--|--|
| Type number                         | Package |  |         |  |  |  |
|                                     | Name    | Description  | Version |  |  |  |
| BYC8B-600P                          | D2PAK   | plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped) | SOT404  |  |  |  |

# 7. Marking

| Table 4. Marking codes |              |
|------------------------|--------------|
| Type number            | Marking code |
| BYC8B-600P             | BYC8B-600P   |

# 8. Limiting values

#### Table 5.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol             | Parameter                           | Conditions   | Min | Max            | Unit               |
|--------------------|-------------------------------------|--|-----|----------------|--------------------|
| V <sub>RRM</sub>   | repetitive peak reverse voltage     |  | -   | 600            | V                  |
| V <sub>RWM</sub>   | crest working reverse voltage       |  | -   | 600            | V                  |
| V <sub>R</sub>     | reverse voltage                     | DC   | -   | 600            | V                  |
| I <sub>F(AV)</sub> | average forward current             | δ = 0.5; T <sub>mb</sub> ≤ 130 °C; square-wave<br>pulse; <u>Fig. 1</u> ; <u>Fig. 2</u> ; <u>Fig. 3</u> | -   | 8              | А                  |
| I <sub>FRM</sub>   | repetitive peak forward current     | δ = 0.5; t <sub>p</sub> = 25 μs; T <sub>mb</sub> ≤ 130 °C;<br>square-wave pulse                        | -   | 16             | A                  |
| I <sub>FSM</sub>   | non-repetitive peak forward current | $t_p$ = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4  | -   | 91             | А                  |
| BYC8B-600P         | All informatic                      | n provided in this document is subject to legal disclaimers.   | (   | NXP N.V. 2014. | All rights reserve |

#### **NXP Semiconductors**

# **BYC8B-600P**

#### Hyperfast power diode

| Symbol           | Parameter            | Conditions   | Min | Мах | Unit |
|------------------|----------------------|--|-----|-----|------|
|                  |                      | $t_p$ = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4 | -   | 100 | A    |
| T <sub>stg</sub> | storage temperature  |  | -65 | 175 | °C   |
| Tj               | junction temperature |  | -   | 175 | °C   |

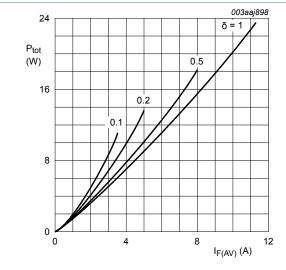
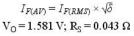
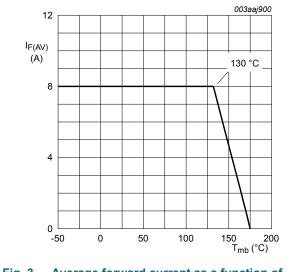


Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values







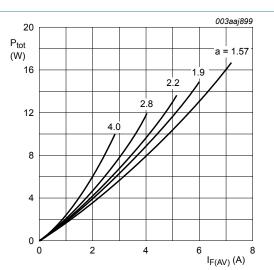
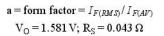
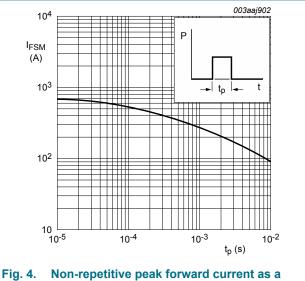


Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values



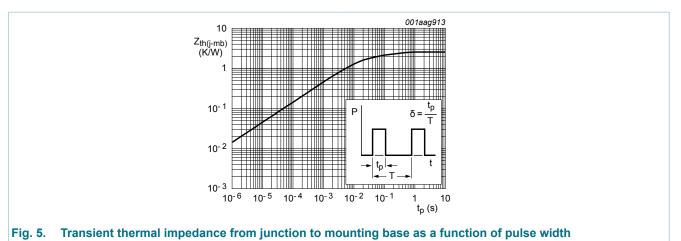


function of pulse width; square waveform; maximum values

Hyperfast power diode

# 9. Thermal characteristics

| Table 6. T            | hermal characteristics                                  |             |     |     |     |      |
|-----------------------|---|-------------|-----|-----|-----|------|
| Symbol                | Parameter   | Conditions  | Min | Тур | Max | Unit |
| R <sub>th(j-mb)</sub> | thermal resistance<br>from junction to<br>mounting base | Fig. 5      | -   | -   | 2.5 | K/W  |
| R <sub>th(j-a)</sub>  | thermal resistance<br>from junction to<br>ambient       | in free air | -   | 60  | -   | K/W  |



# **10. Characteristics**

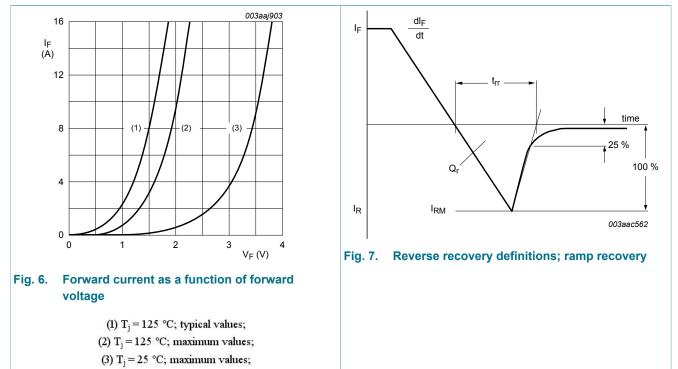
| Symbol                       | Parameter             | Conditions  | Min | Тур | Max | Unit |
|------------------------------|-----------------------|---|-----|-----|-----|------|
| Static char                  | acteristics           | · · · ·   |     |     |     |      |
| V <sub>F</sub>               | forward voltage       | I <sub>F</sub> = 8 A; T <sub>j</sub> = 25 °C; <u>Fig. 6</u>   | -   | -   | 3.4 | V    |
|                              |                       | I <sub>F</sub> = 8 A; T <sub>j</sub> = 125 °C; <u>Fig. 6</u>  | -   | 1.5 | 1.9 | V    |
|                              |                       | I <sub>F</sub> = 8 A; T <sub>j</sub> = 150 °C   | -   | 1.4 | -   | V    |
| I <sub>R</sub> reverse curre | reverse current       | V <sub>R</sub> = 600 V; T <sub>j</sub> = 25 °C  | -   | -   | 20  | μA   |
|                              |                       | V <sub>R</sub> = 600 V; T <sub>j</sub> = 125 °C   | -   | -   | 200 | μA   |
| Dynamic cl                   | haracteristics        | · · · · ·   |     |     |     |      |
|                              | recovered charge      | $I_F = 8 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/\mu\text{s};$<br>$T_j = 25 \text{ °C}; Fig. 7$       | -   | 17  | -   | nC   |
|                              |                       | $I_F$ = 8 A; $V_R$ = 200 V; $dI_F/dt$ = 200 A/µs;<br>T <sub>j</sub> = 125 °C; <u>Fig. 7</u>                           | -   | 90  | -   | nC   |
| t <sub>rr</sub>              | reverse recovery time | I <sub>F</sub> = 1 A; V <sub>R</sub> = 30 V; dI <sub>F</sub> /dt = 200 A/μs;<br>T <sub>i</sub> = 25 °C; <u>Fig. 7</u> | -   | 12  | 18  | ns   |

### **NXP Semiconductors**

# **BYC8B-600P**

#### Hyperfast power diode

| Symbol          | Parameter                     | Conditions  | Min | Тур | Мах | Unit |
|-----------------|-------------------------------|---|-----|-----|-----|------|
|                 |                               | $I_{F} = 8 \text{ A}; V_{R} = 400 \text{ V}; dI_{F}/dt = 500 \text{ A}/\mu\text{s}; T_{j} = 25 \text{ °C}; Fig. 7$      | -   | 19  | -   | ns   |
| I <sub>RM</sub> | peak reverse recovery current | $I_F = 8 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/\mu\text{s};$<br>$T_j = 25 \text{ °C}; Fig. 7$         | -   | -   | 2.2 | A    |
|                 |                               | I <sub>F</sub> = 8 A; V <sub>R</sub> = 200 V; dI <sub>F</sub> /dt = 200 A/μs;<br>T <sub>j</sub> = 125 °C; <u>Fig. 7</u> | -   | -   | 6   | A    |

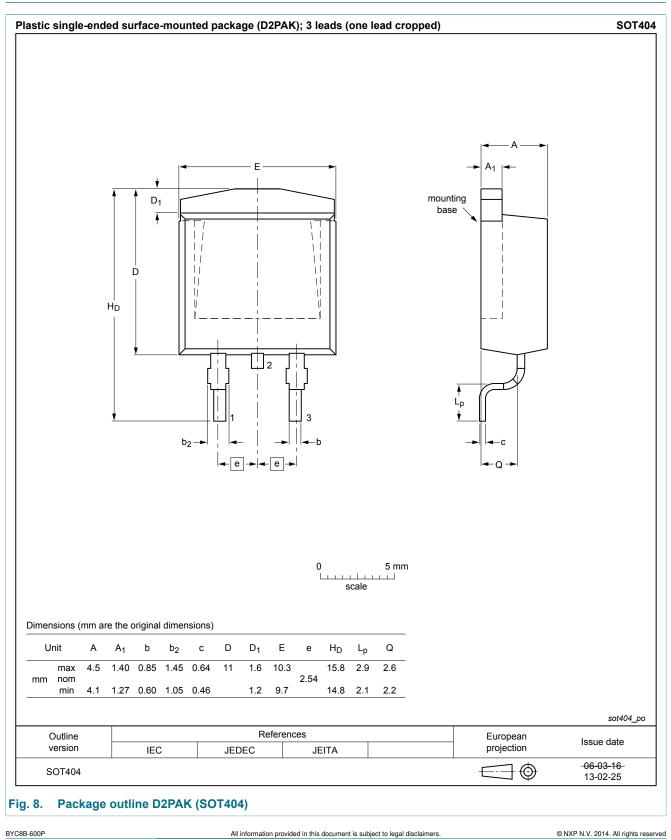


 $V_0 = 1.581 \text{ V}; \text{ R}_S = 0.043 \Omega$ 



Hyperfast power diode

# 11. Package outline



#### Hyperfast power diode

### 12. Legal information

#### 12.1 Data sheet status

| Document status [1][2]               | Product<br>status [3] | Definition  |
|--------------------------------------|-----------------------|---|
| Objective<br>[short] data<br>sheet   | Development           | This document contains data from<br>the objective specification for product<br>development. |
| Preliminary<br>[short] data<br>sheet | Qualification         | This document contains data from the preliminary specification.                             |
| Product<br>[short] data<br>sheet     | Production            | This document contains the product specification.   |

 Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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#### Hyperfast power diode

# **13. Contents**

| 1    | General description     | 1 |
|------|-------------------------|---|
| 2    | Features and benefits   | 1 |
| 3    | Applications            | 1 |
| 4    | Quick reference data    | 1 |
| 5    | Pinning information     | 2 |
| 6    | Ordering information    | 2 |
| 7    | Marking                 | 2 |
| 8    | Limiting values         | 2 |
| 9    | Thermal characteristics | 4 |
| 10   | Characteristics         | 4 |
| 11   | Package outline         | 6 |
| 12   | Legal information       | 7 |
| 12.1 | Data sheet status       | 7 |
| 12.2 | Definitions             | 7 |
| 12.3 | Disclaimers             | 7 |
| 12.4 | Trademarks              | 8 |
|      |                         |   |

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